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## Pauli paramagnetic effect and spin-orbit scattering time in Nb/Al<sub>2</sub>O<sub>3</sub> superconducting multilayers

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## Abstract

The parallel critical field  $H_{c2}||(T)$  of the Nb/Al<sub>2</sub>O<sub>3</sub> two-dimensional (2D) multilayer superconductors has been analyzed by developing the 2D-version of the WHH theory and by utilizing the Takahashi–Tachiki formalism. A reliable method to estimate the spin-orbit scattering time  $\tau_{S0}$  of thin films has been provided. © 2003 Elsevier Science B.V. All rights reserved.

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The parallel orbital critical field  $H_{c2\parallel}(T)$  of thin films is inversely proportional to the thickness d and can be made arbitrary large in principle. Then instead, the spin paramagnetic effect counteracted by spin-orbit scattering limits  $H_{c2\parallel}$ . Accordingly, a reasonable estimation of the spin-orbit scattering time  $\tau_{S0}$  can be made if we properly analyze the  $H_{c2\parallel}(T)$  of thin films. In this paper, we determine  $\tau_{S0}$  of Nb by analyzing  $H_{c2\parallel}$  of the Nb/Al<sub>2</sub>O<sub>3</sub> multilayers.

The Nb/Al<sub>2</sub>O<sub>3</sub> multilayers were prepared by a dual sputtering method [1]. The transition temperature  $T_c$  and the critical fields  $H_{c2\parallel,\perp}$  were determined resistively. The list of the multilayers analyzed in this report is given in Table 1.

Fig. 1 shows the conductance per square,  $G_{\Box}$ , at 10 K as a function of the Nb layer thickness  $d_{Nb}$ .  $G_{\Box}$  exhibits a linear dependence on Nb in both the large and the small  $d_{Nb}$  regions, but the slope of the linear dependence radically changes around  $d_{Nb} = 30$  Å. A similar behavior was first observed in Nb/Ge multilayers [2] and was understood on the basis of a trilayer model. We assume that thin layers of disordered and degraded high resistivity Nb are formed on both interfacial sides of each Nb layer (see the inset in Fig. 1). From the slopes of

the linear dependences of the  $G_{\Box}$  vs.  $d_{\rm Nb}$  line, the resistivities of the degraded layers ( $\rho_{\rm deg}$ ) and the genuine Nb layer ( $\rho_{\rm Nb}$ ) are estimated to be  $\rho_{\rm deg} = 49.5 \,\mu\Omega \text{cm}$  and  $\rho_{\rm Nb} = 7.3 \,\mu\Omega \text{cm}$ , respectively. From the turning point of the slopes, the thickness of each degraded Nb layer,  $d_{\rm Nb}^{\rm deg}$  is estimated to be about 14 Å (totally 28 Å per Nb layer).

Fig. 2 presents  $H_{c2\parallel}(T)$  and  $H_{c2\perp}(T)$  as a function of  $T.H_{c2\parallel}(T)$  rises with an infinite slope at  $T_c$ , showing the two-dimensional (2D) character. The present Nb/Al<sub>2</sub>O<sub>3</sub> multilayers are surely in the dirty limit but not dirty enough to satisfy the condition,  $\lambda_{S0} = 2\hbar/3\pi k_B T_c \tau_{S0} \ge 1$  ( $\lambda_{S0} \sim 0.5$ , for present samples). Then the simplified Maki's theory [3] is not applicable and the 2D version of the full WHH theory [4] must be invoked. The 2D formalism of the WHH theory has been accomplished by Ebisawa [5] and  $H_{c2\parallel}(T)$  of a thin film with the thickness *d* is given by the following equations:

$$\ell n(t) = \psi \left(\frac{1}{2}\right) - \frac{1}{2} \left\{ \left(1 - \frac{\lambda_{S0}}{2G}\right) \psi \left(\frac{1}{2} + \frac{h^2}{t} + \frac{\lambda_{S0}}{4t} + \frac{G}{2t}\right) + \left(1 + \frac{\lambda_{S0}}{2G}\right) \psi \left(\frac{1}{2} + \frac{h^2}{t} + \frac{\lambda_{S0}}{4t} - \frac{G}{2t}\right) \right\},$$
(1)

where  $G = \sqrt{(\lambda_{S0}/2)^2 - 4f\hbar^2}$ ,  $\psi$  is the di-gamma function,  $f = \alpha^2 (d_0/d)^2$ ,  $d_0 = \pi \hbar D/2k_{\rm B}T_{\rm c}$ ,  $\alpha = \hbar/2mD$ ,  $\hbar^2 = \pi \hbar d^2 H^2/12\Phi_0^2 k_{\rm B}T_{\rm c}$ ,  $t = T/T_{\rm c}$ ,  $\Phi_0 = \pi \hbar/e$ , D =electron diffusion constant, m =electron mass, H =applied field (other notations are of standard style). Eq. (1) allows us

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Table 1 Material and superconducting parameters of  $Nb/Al_2O_3$ 

$\frac{d_{Nb}/d_{Al_2O_3}}{(\mathring{A}/\mathring{A})}$	$G_{\square} \ (\Omega_{\square}^{-1})$	<i>T</i> <sub>c</sub> (K)	$\begin{array}{l} \xi(T=0K) \\ (\text{\AA}) \end{array}$	$\frac{\mathrm{d}H_{\mathrm{c}2\perp}/\mathrm{d}T}{\mathrm{(kG/K)}}$	D (cm <sup>2</sup> /s)
10/10	$9.52  imes 10^{-4}$	1.87	87	16.2	0.60
40/40	$1.07  imes 10^{-2}$	3.51	101	6.55	1.50
50/50	$1.77  imes 10^{-2}$	4.60	110	6.25	1.47
60/40	$2.92  imes 10^{-2}$	6.18	109	4.50	2.26
70/70	$4.90  imes 10^{-2}$	6.06	107	4.90	2.00
80/40	$5.71 \times 10^{-2}$	6.55	107	4.11	2.38
100/100	$8.93  imes 10^{-2}$	6.92	107	4.27	2.31



Fig. 1.  $G_{\Box}$  vs.  $d_{\text{Nb}}$ . The inset schematically shows the trilayer structure inside of Nb layers. The shaded parts indicate the degraded Nb layer.  $d_{\text{s}}$  is the effective superconducting layer.



Fig. 2. Examples of measured critical fields and numerical fittings for  $H_{c2\parallel}(T)$  on the basis of Eq. (1) and  $d_s$ .

to calculate  $H_{c2\parallel}(T)$  of thin films in the dirty limit for arbitrary  $\tau_{S0}$  on the basis of  $T_c$ , D,  $\tau_{S0}$  and d values.

Because of the trilayer structure of the Nb sublayer, however, we cannot directly regard  $d_{\text{Nb}}$  as d in Eq. (1). To estimate the effective superconducting film thickness  $d_{\text{s}}$ , we utilized the Takahashi–Tachiki formalism [6] and calculated  $H_{c2\parallel}(T)$  of the sandwiched Nb films (without



Fig. 3. (a) Calculated effective superconducting layer thickness  $d_{\rm s}$  for a unit Nb trilayer as a function of  $d_{\rm Nb}$ . (b) Calculated spin-orbit scattering time  $\tau_{S0}$  vs.  $d_{\rm Nb}$ . Total scattering time  $\tau$  is shown by the dashed line ( $v_{\rm F}^{\rm Nb} = 2.6 \times 10^7$  cm/s).

the paramagnetic effect). The material parameters of Nb ( $\theta_D = 277$  K,  $N = 0.9 \times 10^{23}$ /eVcm<sup>3</sup>,  $V = 0.315 \times 10^{-23}$ eVcm<sup>3</sup>, D = 3.0 cm<sup>2</sup>/s) were used for the central intact Nb layer and those for degraded Nb layer were modified ( $\theta_D = 277$  K,  $N = 0.77 \times 10^{23}$ /eVcm<sup>3</sup>,  $V = 0.252 \times 10^{-23}$ eVcm<sup>3</sup>, D = 0.60 cm<sup>2</sup>/s) to best reproduce the  $T_c$  vs.  $d_{\rm Nb}$  curve [1]. The obtained  $H_{c2\parallel}(T)$  curve was approximated by the G–L result,  $H_{c2\parallel}(T) = \sqrt{12\Phi_0}/2\pi\xi(T)d_s$  ( $\xi(T)$  =coherent length), to get the effective  $d_s$  which is given in Fig. 3(a). Fig. 3(b) presents our final results,  $\tau_{S0}$  as a function of  $d_{\rm Nb}$ . We can conclude that the spin-orbit scattering accounts for 1.2–3% of the total scattering rate in the sputtered Nb. The authors wish to thank Prof. H. Ebisawa for the derivation of Eq. (1).

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